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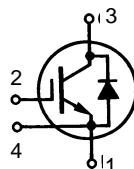
High Voltage IGBT with Diode

IXSN 55N120AU1

$$\begin{aligned} V_{CES} &= 1200 \text{ V} \\ I_{C25} &= 110 \text{ A} \\ V_{CE(sat)} &= 4 \text{ V} \end{aligned}$$

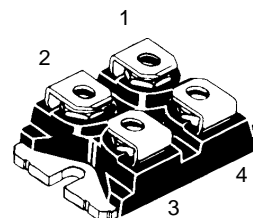
Short Circuit SOA Capability

Preliminary data



Symbol	Test Conditions	Maximum Ratings	
V_{CES}	$T_J = 25^\circ\text{C}$ to 150°C	1200	V
V_{CGR}	$T_J = 25^\circ\text{C}$ to 150°C ; $R_{GE} = 1 \text{ M}\Omega$	1200	A
V_{GES}	Continuous	± 20	V
V_{GEM}	Transient	± 30	V
I_{C25}	$T_C = 25^\circ\text{C}$	110	A
I_{C90}	$T_C = 90^\circ\text{C}$	55	A
I_{CM}	$T_C = 25^\circ\text{C}$, 1 ms	160	A
SSOA (RBSOA)	$V_{GE} = 15 \text{ V}$, $T_{VJ} = 125^\circ\text{C}$, $R_G = 22 \Omega$ Clamped inductive load, $L = 30 \mu\text{H}$	$I_{CM} = 110$ @ $0.8 V_{CES}$	A
t_{SC} (SCSOA)	$V_{GE} = 15 \text{ V}$, $V_{CE} = 0.6 \cdot V_{CES}$, $T_J = 125^\circ\text{C}$ $R_G = 22 \Omega$, non repetitive	10	μs
P_C	$T_C = 25^\circ\text{C}$	IGBT	500 W
P_D		Diode	175 W
V_{ISOL}	50/60 Hz $I_{ISOL} \leq 1 \text{ mA}$	$t = 1 \text{ min}$ $t = 1 \text{ s}$	2500 V~ 3000 V~
T_J		-55 ... +150	$^\circ\text{C}$
T_{JM}		150	$^\circ\text{C}$
T_{stg}		-55 ... +150	$^\circ\text{C}$
M_d	Mounting torque	1.5/13	Nm/lb.in.
	Terminal connection torque (M4)	1.5/13	Nm/lb.in.

miniBLOC, SOT-227 B



Features

- International standard package miniBLOC (ISOTOP) compatible
- Aluminium-nitride isolation
 - high power dissipation
- Isolation voltage 3000 V~
- Low $V_{CE(sat)}$
 - for minimum on-state conduction losses
- Fast Recovery Epitaxial Diode
 - short t_{rr} and I_{RM}
- Low collector-to-case capacitance (< 60 pF)
 - reduces RFI
- Low package inductance (< 10 nH)
 - easy to drive and to protect

Applications

- AC motor speed control
- DC servo and robot drives
- DC choppers
- Uninterruptible power supplies (UPS)
- Switch-mode and resonant-mode power supplies

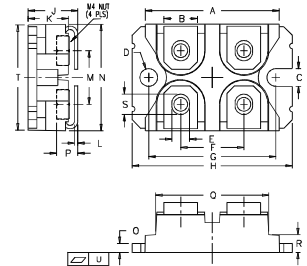
Advantages

- Space savings
- Easy to mount with 2 screws
- High power density

Symbol	Test Conditions	Characteristic Values ($T_J = 25^\circ\text{C}$, unless otherwise specified)		
		min.	typ.	max.
BV_{CES}	$I_C = 8 \text{ mA}$, $V_{GE} = 0 \text{ V}$	1200		V
$V_{GE(th)}$	$I_C = 8 \text{ mA}$, $V_{CE} = V_{GE}$	4		V
I_{CES}	$V_{CE} = 0.8 \cdot V_{CES}$, $T_J = 25^\circ\text{C}$ $V_{GE} = 0 \text{ V}$, $T_J = 125^\circ\text{C}$			1 mA 16 mA
I_{GES}	$V_{CE} = 0 \text{ V}$, $V_{GE} = \pm 20 \text{ V}$			$\pm 200 \text{ nA}$
$V_{CE(sat)}$	$I_C = I_{C90}$, $V_{GE} = 15 \text{ V}$			4 V

Symbol	Test Conditions	Characteristic Values (T _J = 25°C, unless otherwise specified)		
		min.	typ.	max.
g_{fs}	I _C = I _{C90} ; V _{CE} = 10 V, Pulse test, t ≤ 300 μs, duty cycle d ≤ 2 %	32	45	S
I_{C(on)}	V _{CE} = 10 V, V _{GE} = 15 V		340	A
C_{ies}	V _{CE} = 25 V, V _{GE} = 0 V, f = 1 MHz		8000	pF
C_{oes}			590	pF
C_{res}			90	pF
Q_g	I _C = I _{C90} ; V _{GE} = 15 V, V _{CE} = 0.5 V _{CES}		300	nC
Q_{ge}			80	nC
Q_{gc}			140	nC
t_{d(on)}	Inductive load, T_J = 25°C I _C = I _{C90} ; V _{GE} = 15 V, V _{CE} = 0.8 • V _{CES} ; R _G = 2.7 Ω Remarks: Switching times may increase for V _{CE} (Clamp) > 0.8 • V _{CES} , higher T _J or increased R _G		140	ns
t_{ri}			220	ns
t_{d(off)}			400	ns
t_{fi}			700	1000 ns
E_{off}			18	mJ
t_{d(on)}	Inductive load, T_J = 125°C I _C = I _{C90} ; V _{GE} = 15 V, V _{CE} = 0.8 • V _{CES} ; R _G = 2.7 Ω Remarks: Switching times may increase for V _{CE} (Clamp) > 0.8 • V _{CES} , higher T _J or increased R _G		140	ns
t_{ri}			250	ns
t_{d(off)}			600	ns
t_{fi}			900	ns
t_c			950	ns
E_{on}			6	mJ
E_{off}		25	mJ	
R_{thJC}			0.25	K/W
R_{thCK}		0.05		K/W

miniBLOC, SOT-227 B



M4 screws (4x) supplied

Dim.	Millimeter		Inches	
	Min.	Max.	Min.	Max.
A	31.50	31.88	1.240	1.255
B	7.80	8.20	0.307	0.323
C	4.09	4.29	0.161	0.169
D	4.09	4.29	0.161	0.169
E	4.09	4.29	0.161	0.169
F	14.91	15.11	0.587	0.595
G	30.12	30.30	1.186	1.193
H	38.00	38.23	1.496	1.505
J	11.68	12.22	0.460	0.481
K	8.92	9.60	0.351	0.378
L	0.76	0.84	0.030	0.033
M	12.60	12.85	0.496	0.506
N	25.15	25.42	0.990	1.001
O	1.98	2.13	0.078	0.084
P	4.95	5.97	0.195	0.235
Q	26.54	26.90	1.045	1.059
R	3.94	4.42	0.155	0.174
S	4.72	4.85	0.186	0.191
T	24.59	25.07	0.968	0.987
U	-0.05	0.1	-0.002	0.004

Reverse Diode (FRED)

Characteristic Values
(T_J = 25°C, unless otherwise specified)

Symbol	Test Conditions	Characteristic Values		
		min.	typ.	max.
V_F	I _F = I _{C90} ; V _{GE} = 0 V, Pulse test, t ≤ 300 μs, duty cycle d ≤ 2 %		2.55	V
I_{RM}	I _F = I _{C90} ; V _{GE} = 0 V, -di _F /dt = 480 A/μs V _R = 540 V T _J = 100°C I _F = 1 A; -di/dt = 200 A/μs; V _R = 30 V T _J = 25°C		32	A
t_{rr}			300	ns
			40	60 ns
R_{thJC}			0.71	K/W